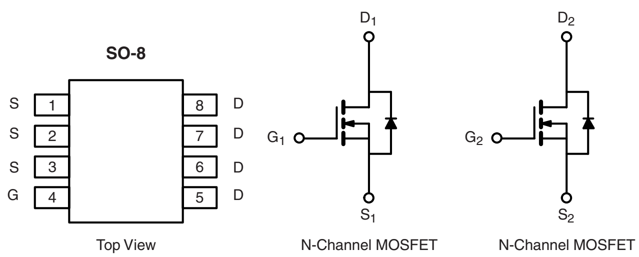
Automotive
Dual N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.036
I_D (A)	5.9
Configuration	Dual



FEATURES

- **Halogen-free**
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance

Pb-free
RoHS COMPLIANT

AEC-Q101 RELIABILITY

- Passed all AEC-Q101 Reliability Testing
- Characterization Ongoing

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and Halogen-free	SQ4936EY-T1-GE3

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current[a]	T_C = 25 °C	I_D	4.4	A
	T_C = 70 °C		3.6	
Continuous Source Current (Diode Conduction)[a]		I_S	0.9	
Pulsed Drain Current[b]		I_{DM}	± 30	
Single Pulse Avalanche Energy	L = 0.1 mH	E_{AS}	-	mJ
Single Pulse Avalanche Current		I_{AS}	-	A
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	1.1	W
	T_A = 70 °C		0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	110	°C/W
Junction-to-Case (Drain)		R_{thJC}	40	

Notes
a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).

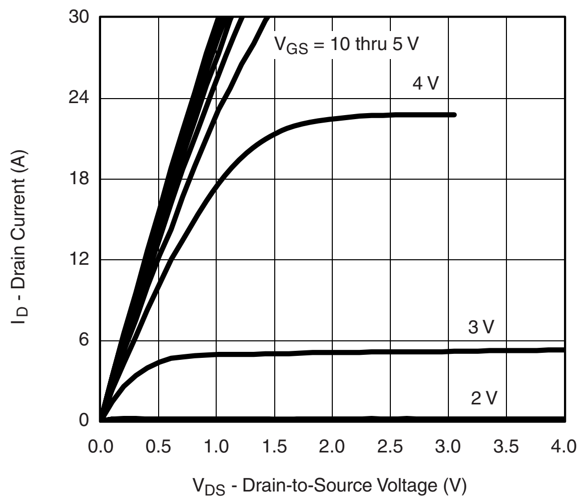
SPECIFICATIONS T_C = 25 °C, unless otherwise noted							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		-	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA		1.0	-	3.0	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 30 V	-	-	1.0	µA
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 55 °C	-	-	5	
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 175 °C	-	-	-	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V	$V_{DS} \geq$ 5 V	30	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 5.9 A	-	0.0032	0.0036	Ω
		V_{GS} = 10 V	I_D = 30 A, T_J = 125 °C	-	-	-	
		V_{GS} = 10 V	I_D = 30 A, T_J = 175 °C	-	-	-	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A		-	15	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	-	-	pF
Output Capacitance	C_{oss}			-	-	-	
Reverse Transfer Capacitance	C_{rss}			-	-	-	
Total Gate Charge[c]	Q_g	V_{GS} = 10 V	V_{DS} = 15 V, I_D = 5.9 A	-	13	-	nC
Gate-Source Charge[c]	Q_{gs}			-	2.3	-	
Gate-Drain Charge[c]	Q_{gd}			-	2.0	-	
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		-	6	-	ns
Rise Time[c]	t_r			-	14	-	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	30	-	
Fall Time[c]	t_f			-	5	-	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]							
Pulsed Current[a]	I_{SM}			-	-	-	A
Forward Voltage	V_{SD}	I_F = 85 A, V_{GS} = 0 V		-	-	-	V
Reverse Recovery Time	t_{rr}	I_F = 1.7 A, dI/dt = 100 A/µs		-	30	-	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			-	-	-	A
Reverse Recovery Charge	Q_{rr}			-	-	-	µC

Notes

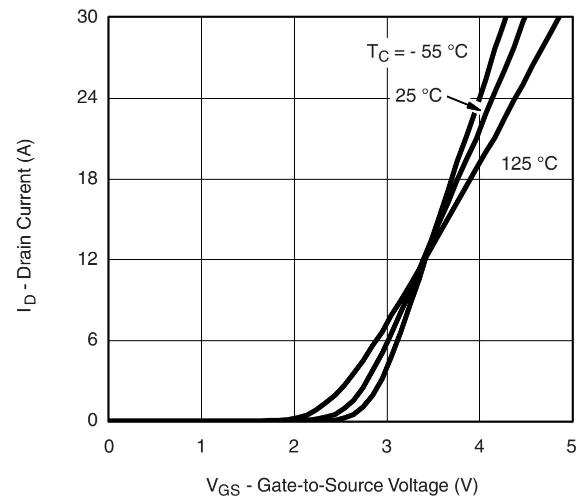
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

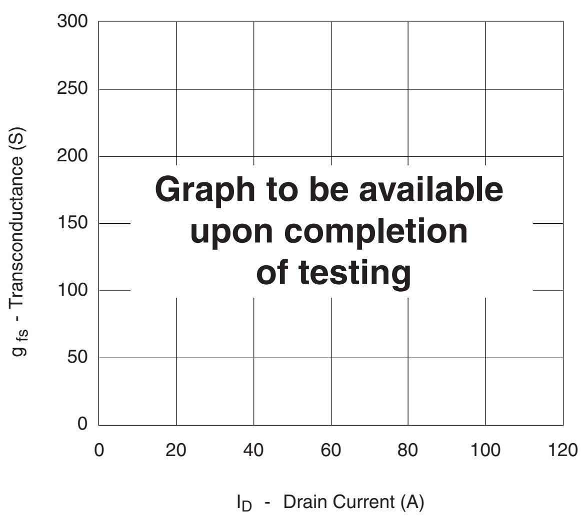
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



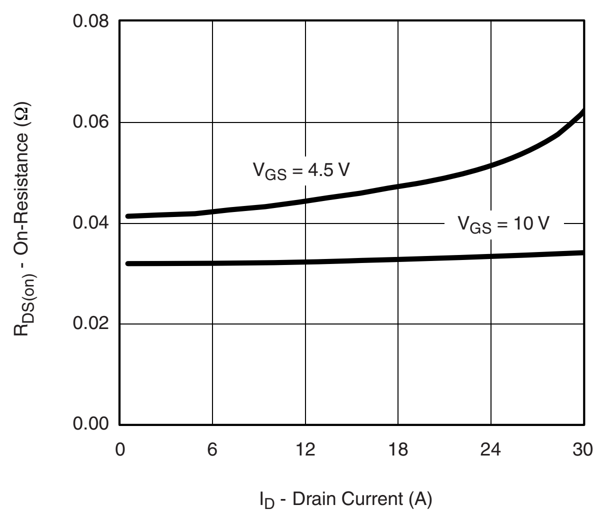
Output Characteristics



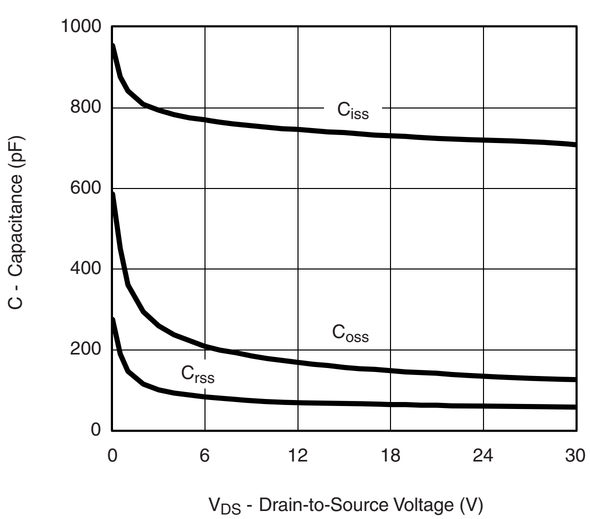
Transfer Characteristics



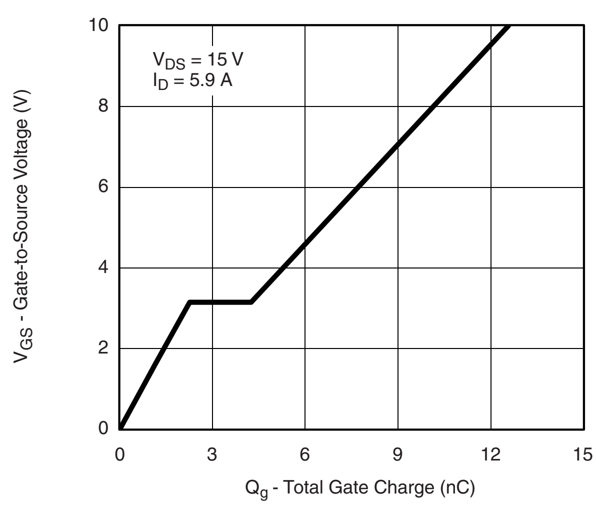
Transconductance



On-Resistance vs. Drain Current

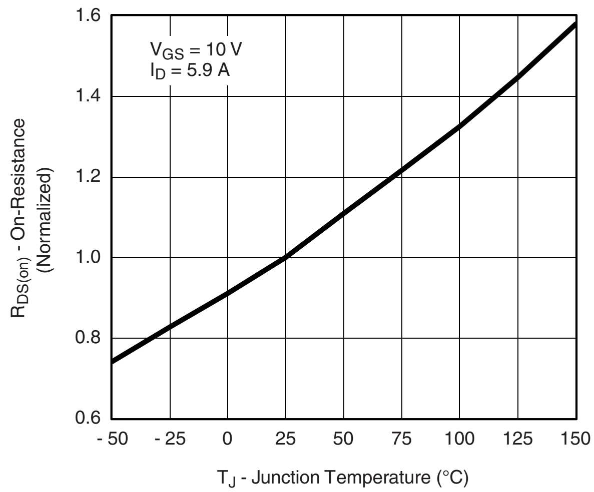


Capacitance

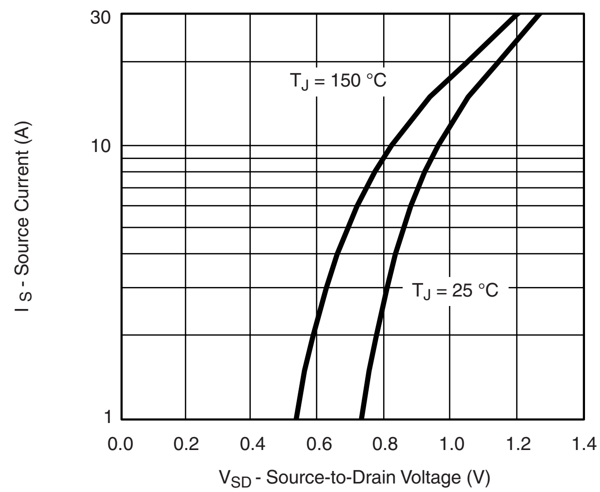


Gate Charge

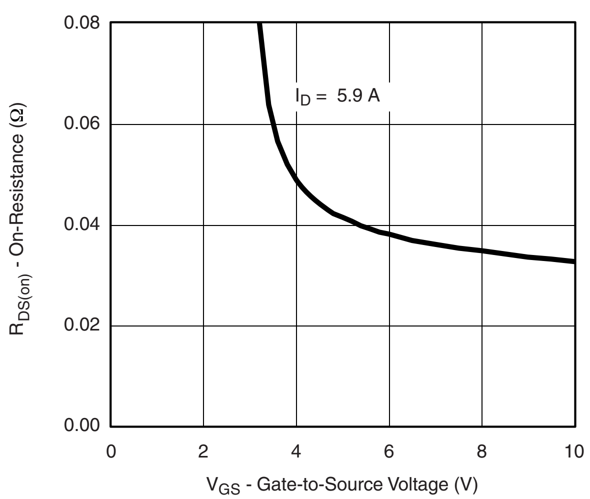
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



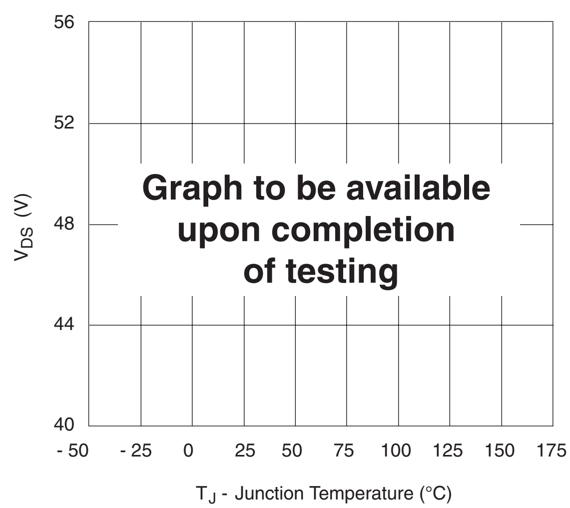
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage

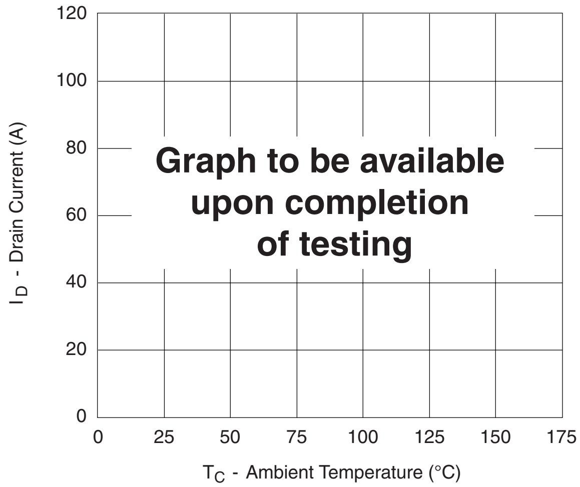


On-Resistance vs. Gate-to-Source Voltage

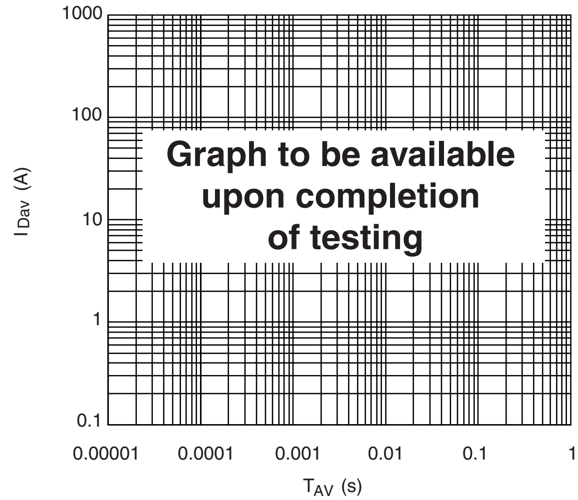


Drain Source Breakdown vs. Junction Temperature

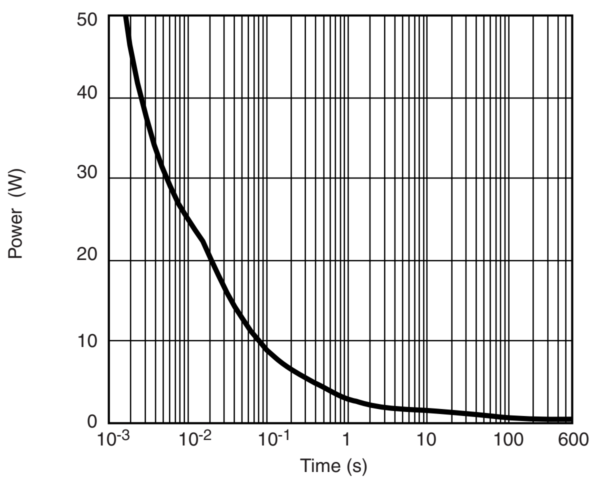
THERMAL RATINGS T_A = 25 °C, unless otherwise noted



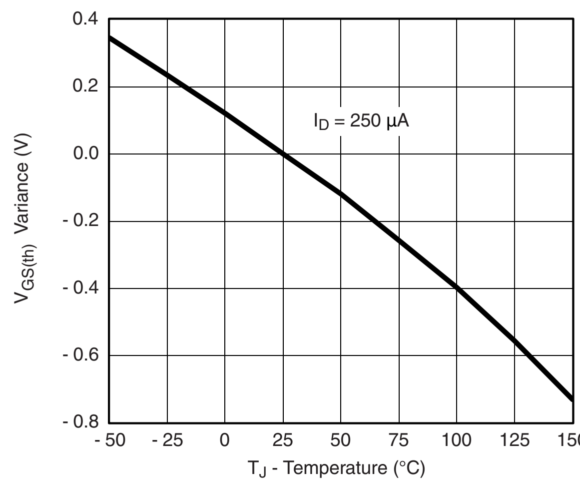
Maximum Drain Current vs. Ambient Temperature



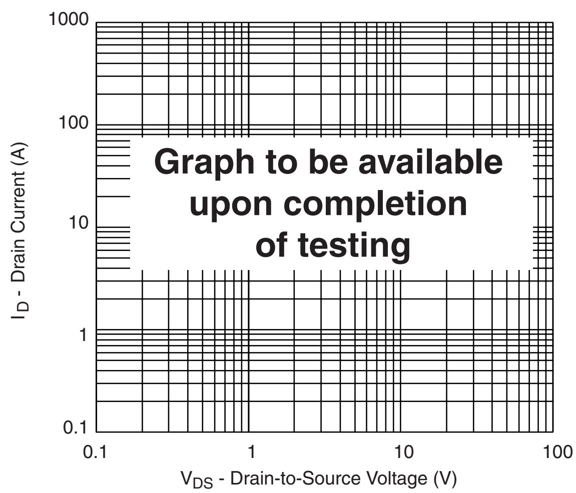
Avalanche Current vs. Time



Single Pulse Power, Junction-to-Ambient



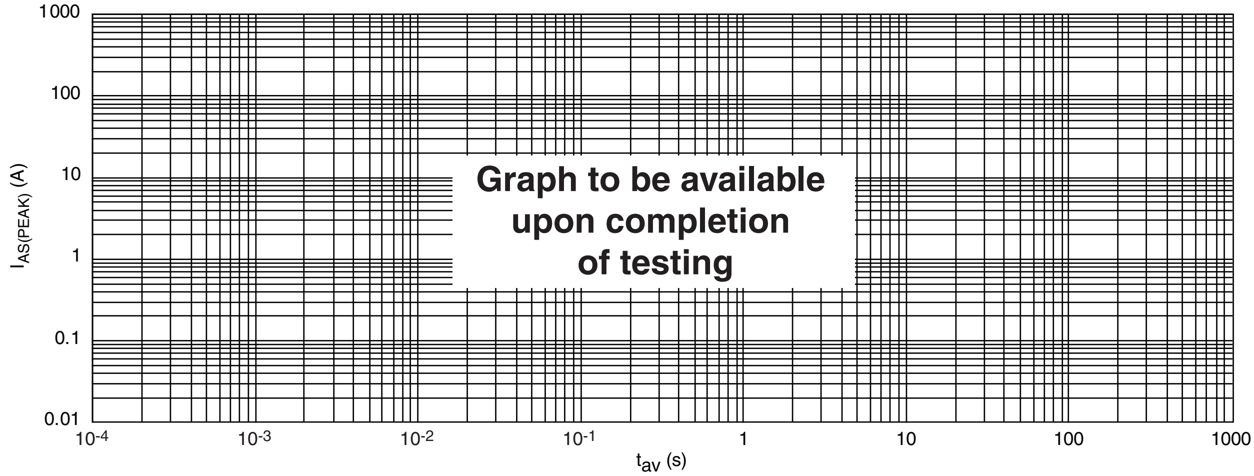
Threshold Voltage



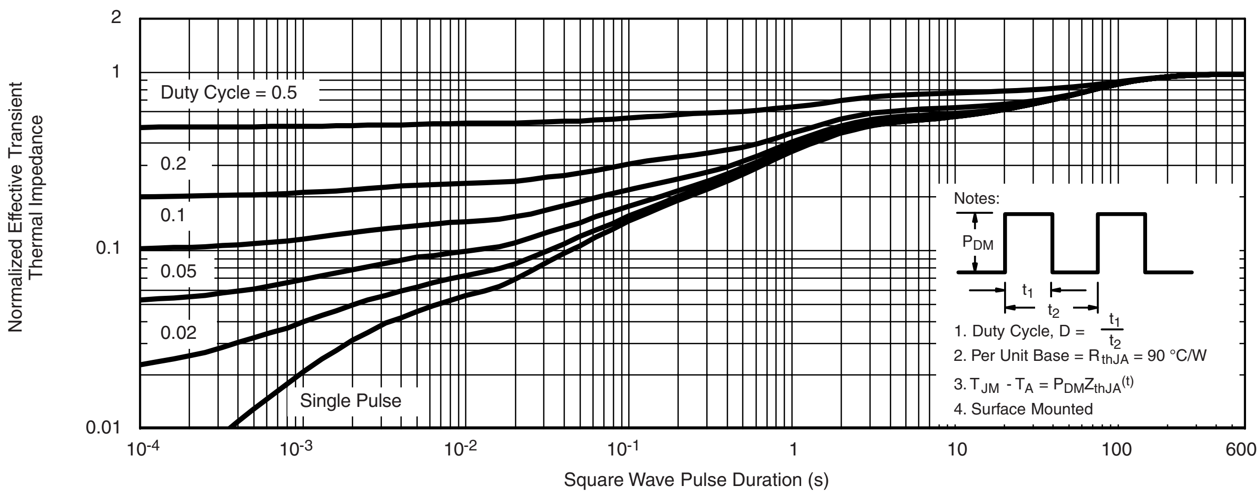
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

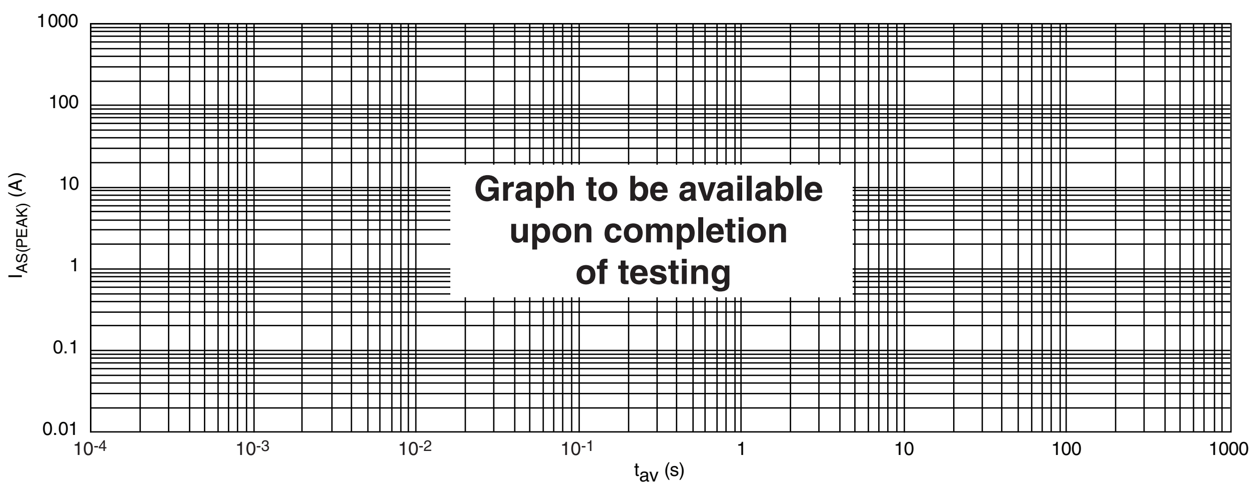
THERMAL RATINGS T_A = 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

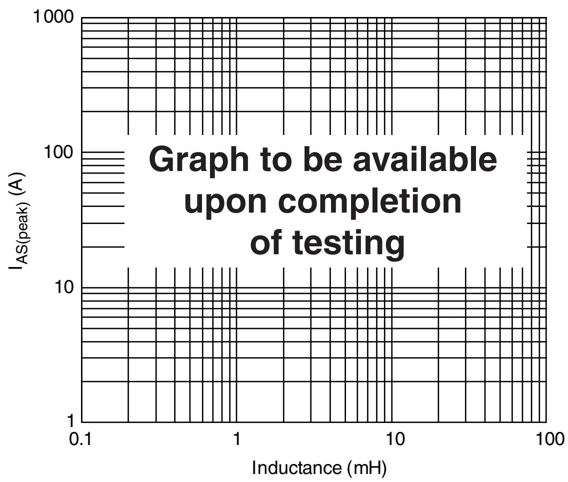


Normalized Thermal Transient Impedance, Junction-to-Ambient

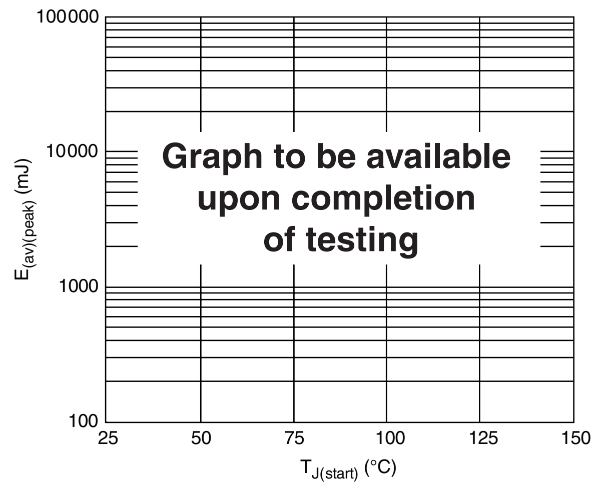


Single Pulse Avalanche Current (Peak) vs. Time in Avalanche

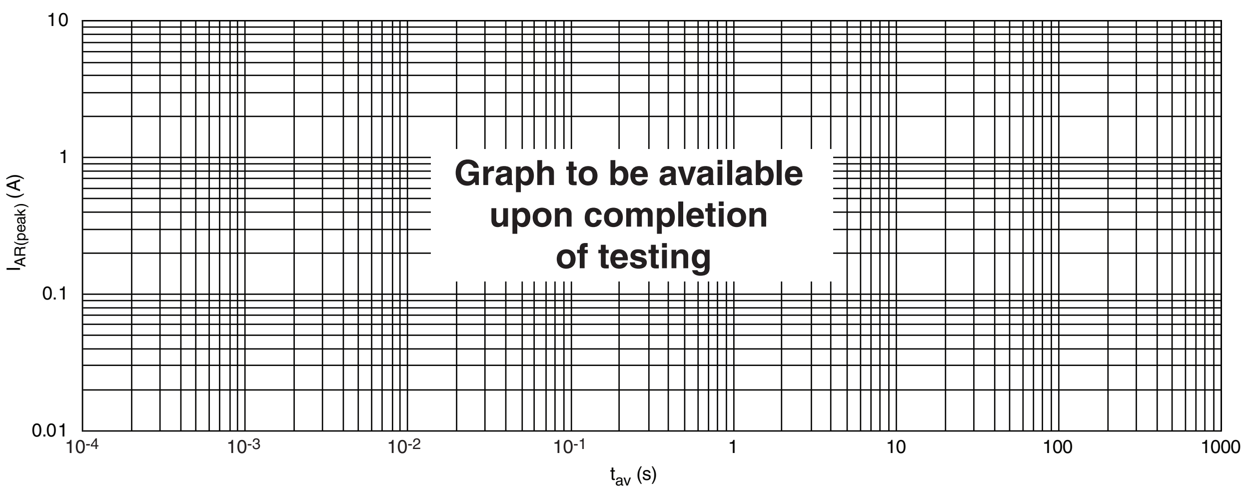
THERMAL RATINGS T_A = 25 °C, unless otherwise noted



Single Pulse Avalanche Current (Peak) vs. Inductance

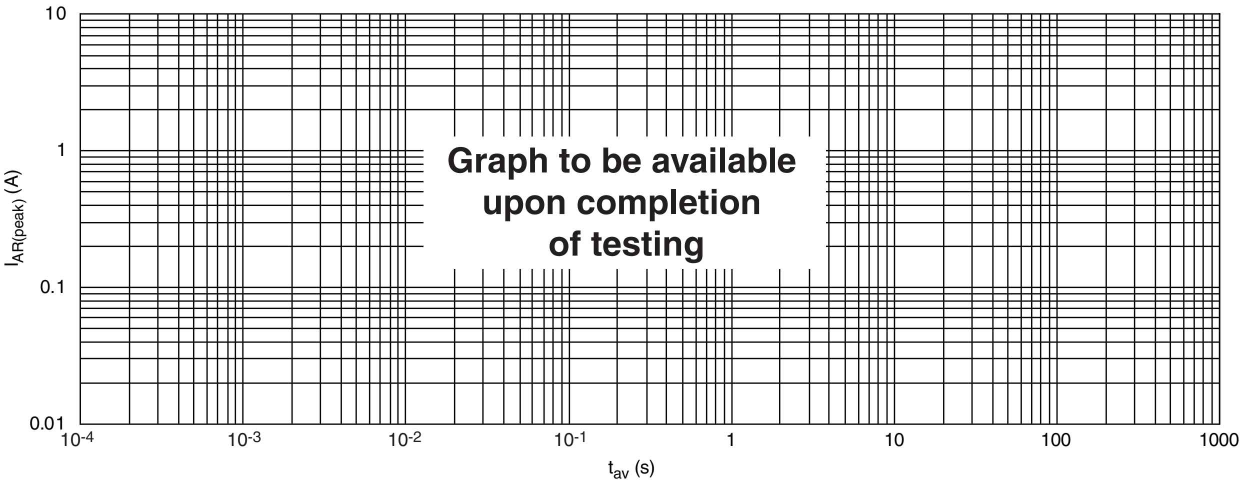


Single Pulse Avalanche Energy (Peak) vs. $T_{J(start)}$



Repetitive Avalanche Current (Peak) vs. Time in Avalanche at T_A = 25 °C

THERMAL RATINGS T_A = 25 °C, unless otherwise noted



Repetitive Avalanche Current (Peak) vs. Time in Avalanche at T_A = 150 °C

Note

The characteristics shown in the six graphs
- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Single Pulse Avalanche Current (Peak) vs. Time in Avalanche
- Single Pulse Avalanche Current (Peak) vs. Inductance
- Single Pulse Avalanche Energy (Peak) vs. $T_{J\ (start)}$
- Repetitive Avalanche Current (Peak) vs. Time in Avalanche at T_A = 25 °C
- Repetitive Avalanche Current (Peak) vs. Time in Avalanche at T_A = 150 °C

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?68868.

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.